

MONDAY 19 SEPTEMBER 2022

08:00-09:00	REGISTRATION + MORNING REFRESHMENTS
09:00-09:15	OPENING REMARKS
SESSION 1 – PHOTONICS 1	
09:15-10:15	<i>Ovshinsky Award: Harish Bhaskaran</i> <i>Ovshinsky Award: David Wright</i>
10:15-10:30	Mengyun Wang – University of Oxford <i>Reconfigurable metasurfaces using lossless phase-change material</i>
10:30-10:45	Euan Humphreys – University of Exeter <i>Filtering and Modulation from Visible to Terahertz using Phase-Change Extraordinary Optical Transmission Metasurfaces</i>
10:45-11:20	COFFEE BREAK
SESSION 2 – PHOTONICS 2	
11:20-11:45	<i>Invited Speaker</i> Arka Majumdar – University of Washington
11:45-12:00	June Sang Lee – University of Oxford <i>Polarization-selective tunability in hybrid phase-change nanowires</i>
12:00-12:15	Zhuoran Fang – University of Washington <i>Ultra-low energy programmable non-volatile silicon photonics based on graphene heaters</i>
12:15-12:30	Daniel Yimam – University of Groningen <i>Structural colors and enhanced resolution at the nanoscale: Local structuring of phase change materials using focused ion beam</i>
12:30-12:55	<i>Invited Speaker</i> Otto Muskens – University of Southampton
12:55-13:00	GROUP PHOTO
13:00-15:00	LUNCH BREAK & POSTER PRESENTATIONS
SESSION 3 - DRIFT	
15:00-15:25	<i>Invited Speaker</i> Ghazi Sarwat Syed – IBM Research (Zurich) <i>Phase Change Computational Memory: the Materials of it</i>
15:25-15:40	Benedikt Kersting – IBM Research (Zurich) <i>Many-body thermal excitation and the collective relaxation model</i>
15:40-15:55	Konstantinos Konstantinou – Tampere University <i>Intrinsic electron and hole trapping in amorphous phase-change memory materials: connection to resistance drift</i>
15:55-16:10	Eilam Yalon – Israel Institute of Technology <i>Low Resistance Drift Multi-Level PCM By Constant Amplitude Sub-Nanosecond Reset Pulses</i>
16:10-16:45	COFFEE BREAK
SESSION 4 - IN-MEMORY COMPUTING	
16:45-17:10	<i>Invited Speaker</i> Irem Boybat – IBM Research (Zurich)
17:10-17:35	<i>Invited Speaker</i> Nicole Saulnier – IBM Research (Albany, NY)
17:35-17:50	Bokusui Nakayama – Keio University (Japan) <i>Mimicking the Pheromone Communication of Ant Swarm with Colloids and Phase Change Material</i>

TUESDAY 20 SEPTEMBER 2022

08:30-09:00 REGISTRATION + MORNING REFRESHMENTS

SESSION 5 - THEORY

- 09:00-09:25 *Invited Speaker* Riccardo Mazzarello – University of Rome
Atomistic study of the configurational entropy of supercooled liquid GeTe
- 09:25-09:40 Wei Zhang – Xi'an Jiaotong University
Unraveling crystallization mechanisms and electronic structure of Ge-Sb-Te alloys by ab initio simulations
- 09:40-09:55 Stephen Elliott – University of Cambridge
Hyperbonding in telluride memory materials
- 09:55-10:10 Carl-Friedrich Schön – RWTH Aachen University
Chemical Bonding revisited: The Potential of Property Maps
- 10:10-10:25 Matthias Wuttig – RWTH Aachen University
Phase Change Materials by Design: Developing Treasure Maps with Quantum Chemistry
- 10:25-10:40 Xian-Bin Li – Jilin University
Entropy barrier controlled ultrafast reversible ferroelectric phase change in 2D III2-VI3 materials

10:40-11:15 COFFEE BREAK

SESSION 6 - GE-RICH GST

- 11:15-11:40 *Invited Speaker* Marco Bernasconi – Università di Milano-Bicocca
Atomistic simulations of the crystallization kinetics: Sb in confined geometry and asdep GeTe
- 11:40-11:55 Eloïse Rahier – CEMES-CNRS and Université de Toulouse
Crystallization mechanism of Ge-rich GST unveiled by in-situ synchrotron XRD and (S)TEM.
- 11:55-12:10 Elisa Petroni – STMicroelectronics
Advanced metrics for quantification of by-process segregation beyond ternary systems
- 12:10-12:35 *Invited Speaker* Stefano Cecchi – Università di Milano-Bicocca
- 12:35-12:50 Sabrina Calvi – University of Tor Vergata
Ge-Sb-Te alloys on free-standing flexible substrates

12:50-14:50 LUNCH BREAK & POSTER PRESENTATIONS

SESSION 7 - ePCM

- 14:50-15:15 *Invited Speaker* Andrea Redaelli – STMicroelectronics
- 15:15-15:30 Martina Tomelleri – STMicroelectronics
Investigation of N-doped GeSe_{0.5}Te_{0.5} films for Embedded Phase-Change Memories
- 15:30-15:45 Fabrizio Arciprete – University of Tor Vergata
Electronic properties, interface formation and Sb confinement in In-based PCM heterostructures
- 15:45-16:10 *Invited Speaker* Pierre Noé – CEA Grenoble (LETI)
Phase-Change and Ovonic Chalcogenide Materials: Unique and Uncommon Physical Properties behind Innovative Electronic and Photonic Devices

16:10-16:45 COFFEE BREAK

SESSION 8 - THERMAL ENGINEERING

- 16:45-17:10 *Invited Speaker* Rossella Ranica – STMicroelectronics
Optimization of Heater system in ePCM for robust reliability and scalability in 28nm FDSOI technology
- 17:10-17:25 Rob Simpson – Singapore University of Technology and Design
Thermally Engineered Phase Change Materials and Superlattices
- 17:25-17:50 *Invited Speaker* Eric Pop – Stanford University
Thermal Confinement and Low-Power Memory Devices Based on Superlattice Chalcogenides

19:30 GALA DINNER

WEDNESDAY 21 SEPTEMBER 2022

08:00-08:40 MORNING REFRESHMENTS

SESSION 9 – OTS & MULTILAYERS

08:40-09:05 *Invited Speaker* Elia Ambrosi – TSMC

09:05-09:20 Chanyoung Yoo – Seoul National University
Atomic Layer Deposition of GeTe/Sb₂Te₃ Superlattice and Its Switching Mechanism

09:20-09:35 Michelle Huai-Yu Cheng – Macronix International Co., LTD
Multilayer InAsSeGe OTS Selectors Engineering for High Thermal Stability and Improved Endurance 3D Crosspoint Memory

09:35-10:00 *Invited Speaker* Hyunsang Hwang – Pohang University of Science and Technology (POSTECH)
Switching Mechanism of Ovonic Threshold Switch Devices

10:00-10:35 COFFEE BREAK

SESSION 10 – OTS & MULTILAYERS

10:35-11:00 *Invited Speaker* Taras Ravsher – IMEC
Polarity-dependent effects in OTS materials and their application as self-selective memory

11:00-11:15 Damien Terebenec – CEA Grenoble (LETI)
PCM Heterostructures for Low Power Phase-Change Memory: from multilayers to van der Waals stacks

11:15-11:30 Vitomir Sever – CEA Grenoble (LETI)
HAADF-STEM analysis of the local structure of GeTe-Sb₂Te₃ heterostructures obtained by van der Waals epitaxy

11:30-11:45 Jaemin Park – Korea University
Sb₂Te₃/TiTe₂ superlattice like based phase change memory

11:45-12:10 *Invited Speaker* Min Zhu – Shanghai Institute of Microsystem and Information Technology
Single Element Switch

12:10-12:30 BREAK

12:30-13:00 **AWARD CEREMONY & CLOSING**

13:00-14:00 LUNCH & END

POSTER INDEX

- P-01 Julian Mertens
Confinement induced coherent phonon softening in Sb₂Te₃ thin films
- P-02 Jaeyeon Kim
Filamentary Threshold Switching in an Amorphous Ga₂Te₃ Film
- P-03 Roopali Shekhawat
Rhombohedral to Orthorhombic transformation in phase change GeTe-GeSe
- P-04 Wansun Kim
Threshold Switching of (ZnTe)_x(CrTe)_{1-x} Thin Films
- P-05 Chang Woo Lee
Phase change in GeTe/Sb₂Te₃ superlattices: formation of the vacancy-ordered metastable cubic structure via Ge migration
- P-06 Jeong Woo Jeon
Fabrication of Vertical-type Phase-change Memory Using Atomic Layer Deposition
- P-07 Byongwoo Park
Atomic layer deposition (ALD) of GeSe₂ for ovonic threshold switch with a low off current density
- P-08 Sangmin Jeon
Enhanced Atomic Layer Deposition of Antimony-Trichalcogenides by Ammonia Co-injection
- P-09 Wonho Choi
Parallel Integration of nano-scale Atomic Layer Deposited Ge₂Sb₂Te₅ Phase-change Memory with Indium Gallium Zinc Oxide Thin-film Transistor
- P-10 Gwangsik Jeon
Atomic Layer Deposition of Manganese Telluride Thin Films for Phase-change Memory
- P-11 Anthony Albanese
Amorphous Chalcogenide Thin Films: From Bonding Mechanism To On-Chip Highly Non-Linear Photonic Devices
- P-12 Dasol Kim
Reshape operating room for speed, energy, and reliability
- P-13 Giuseppe Darrigo
Innovative Graphene nano-electrodes for Phase Change Memory applications
- P-14 Alain Portavoce
Kinetic Monte Carlo simulations of Ge-rich GST thin film crystallization
- P-15 Sebastian Walfort
Spanning femtoseconds to seconds in the photoinduced response of antimony thin films
- P-16 Nur Qalishah Adanan
Amorphization dependent recrystallization of Sb₂Te₃
- P-17 Yuyu Jiang
Compact high-speed on-chip microwave system: from the perspective of tunable passive devices
- P-18 Guillaume Roland
New insights in GeTe growth mechanisms

- P-19 Arun Kumar
Structural and Interface analysis of Ge-(Sb)-Te/Sb₂Te₃ core-shell nanowires grown by MOCVD
- P-20 Md Tashfiq Bin Kashem
Modeling Phase Change Memory Devices
- P-21 Nils Holle
Influence of density on elemental antimony glass
- P-22 Flavia Righi Riva
Interdiffusion at the interface in thermally stable Ge-Sb-Te heterostructures: a photoemission study
- P-23 Suyoun Lee
Gate-tunable three-terminal Ovonic threshold switch (OTS) for a highly-scalable artificial retinal ganglion cell (RGC)
- P-24 Peter Kerres
Combinatorial Material Synthesis of Chalcogenides by Sputter Deposition: A case study of the Sb-Te Binary Line
- P-25 Anbarasu Manivannan
Realization of Tunable Reflective Optical Limiter using GeTe Phase Change Material
- P-26 George Braid
Lens Numerical Aperture Control with Phase-Change Metasurfaces
- P-27 Joe Shields
Phase-change spatial light modulators with amplitude-only control
- P-28 J. Luchtenveld
Phase-change properties of ultrathin PLD-fabricated GeSb_{100-x} thin films
- P-29 Jessy Paterson
Electronic and thermal transport in nanocomposite phase-change material thin films
- P-30 Akash Patil
Raman Thermometry Characterization of GeSbTe Based Phase Change Materials
- P-31 Роман Степанов
Van der Waals interactions in ab-initio studies of two dimensional functional chalcogenides
- P-32 Angel-Theodor Buruiana
Exhaustive in-situ evaluation of phase transitions in GST 225 thin films
- P-33 Yuxing Zhou
Ab initio molecular dynamics simulations of Ge-rich Ge-Sb-Te alloys
- P-34 Hao Tong
Trade-off between multi-level characteristics and power consumption of high aspect ratio phase change memory
- P-35 Samarth Aggarwal
Reconfigurable Silicon Carbide photonics using Phase Change Materials
- P-36 Yuhan He
Ultra-Efficient Plasmonic Phase-Change Devices by Improved Mode Coupling
- P-37 Utku Emre Ali
Phase Change Nanowires as Tunable NEMS